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				First Named Inventor:	Aaditya Mahajan
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Sheet	1	of	1	Attorney Docket Number	TRQ-12957

U.S. PUBLISHED PATENT APPLICATIONS

Examiner Initials*	Cited No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Bollaert et al., "Metamorphic In _{0.4} Al _{0.6} As/In _{0.4} Ga _{0.6} As HEMT's on GaAs Substrate", IEEE Electron Device Letters, Vol. 20, No. 3, March 1999, pp. 123-125.
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EXAMINER	DATE CONSIDERED

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